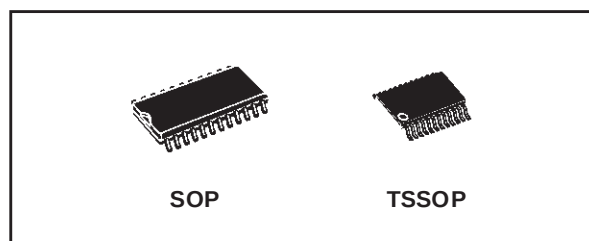


OCTAL DUAL SUPPLY BUS TRANSCEIVER

- HIGH SPEED: $t_{PD} = 8ns$ (MAX.) at $T_A=25^{\circ}C$
 $V_{CCA} = 3.3V$ $V_{CCB} = 5.0V$
- LOW POWER DISSIPATION:
 $I_{CCA} = I_{CCB} = 5\mu A$ (MAX.) at $T_A=25^{\circ}C$
- LOW NOISE: $V_{OLP} = 0.3V$ (TYP.) at
 $V_{CCA}=3.3V$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 24mA$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CCA}(OPR) = 2.7V$ to $3.6V$ (1.2V Data Retention)
 $V_{CCB}(OPR) = 2.7V$ to $5.5V$ (1.2V Data Retention)
 PIN AND FUNCTION COMPATIBLE WITH
 74 SERIES C3245
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74LVXC3245 is a dual supply 8 bit configurable low voltage CMOS OCTAL BUS TRANSCEIVER fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. Designed for use as an interface between a 3.3V bus and a 3.3V to 5V bus in a mixed 3.3V/5V supply systems, it achieves high speed operation while maintaining the CMOS low power dissipation.



ORDER CODES

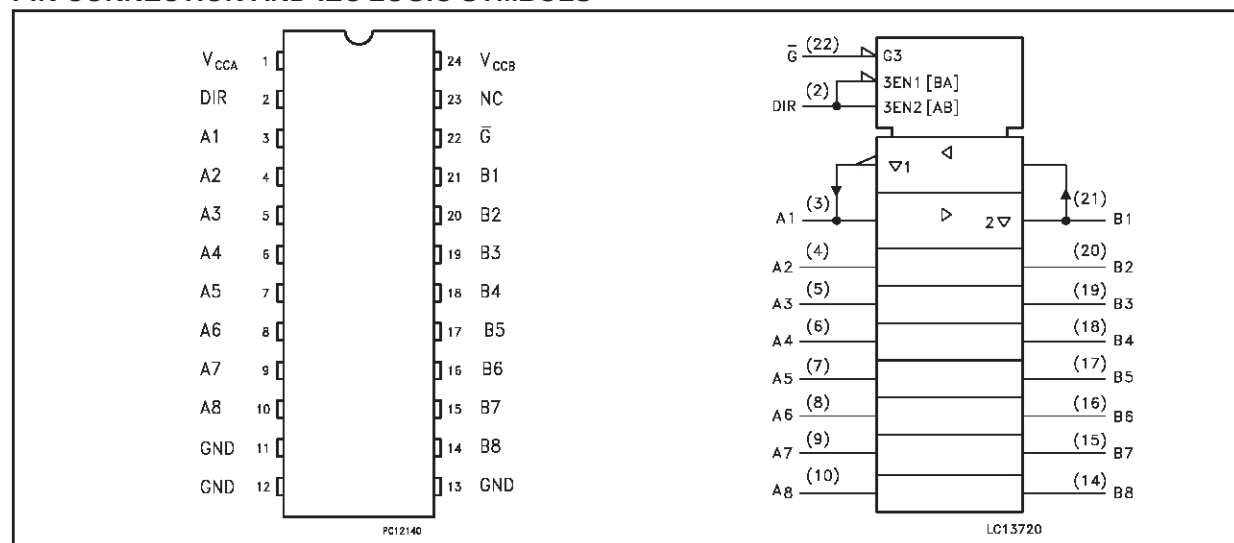
PACKAGE	TUBE	T & R
SOP	74LVXC3245M	74LVXC3245MTR
TSSOP		74LVXC3245TTR

This IC is intended for two-way asynchronous communication between data buses and the direction of data transmission is determined by DIR input. The enable input $\bar{G}$ can be used to disable the device so that the buses are effectively isolated.

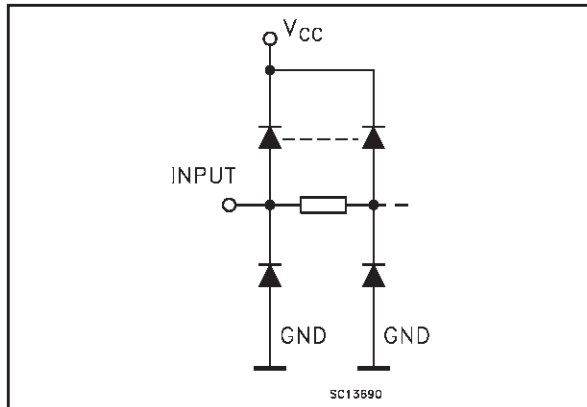
The A-port interfaces with the 3V bus, the B-port with the 5V bus.

All inputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME QND FUNCTION
2	DIR	Directional Control
3, 4, 5, 6, 7, 8, 9, 10	A1 to A8	Data Inputs/Outputs
21, 20, 19, 18, 17, 16, 15, 14	B1 to B8	Data Inputs/Outputs
22	$\overline{G}$	Output Enable Input
11, 12, 13	GND	Ground (0V)
23	NC	Not Connected
1	V _{CCA}	Positive Supply Voltage
24	V _{CCB}	Positive Supply Voltage

TRUTH TABLE

INPUTS		FUNCTION		OUTPUT
$\overline{G}$	DIR	A BUS	B BUS	
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	Z	Z	Z

X=Don't care; Z=High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CCA}	Supply Voltage	-0.5 to +7.0	V
V _{CCB}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to V _{CCA} + 0.5	V
V _{I/OA}	DC I/O Voltage	-0.5 to V _{CCA} + 0.5	V
V _{I/OB}	DC I/O Voltage	-0.5 to V _{CCB} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 50	mA
I _{OA}	DC Output Current	± 50	mA
I _{OB}	DC Output Current	± 50	mA
I _{CCA}	DC V _{CC} or Ground Current	± 200	mA
I _{CCB}	DC V _{CC} or Ground Current	± 100	mA
P _d	Power Dissipation	180	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Rating are those value beyond which damage to the device may occur. Functional operation under these condition is not implied

(*) 500mW: ≡ 65°C derated to 300mW by 10mW/°C: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CCA}	Supply Voltage (note 1)	2.7 to 3.6	V
V_{CCB}	Supply Voltage (note 1)	2.7 to 5.5	V
V_I	Input Voltage	0 to V_{CCA}	V
$V_{I/OA}$	I/O Voltage	0 to V_{CCA}	V
$V_{I/OB}$	I/O Voltage	0 to V_{CCB}	V
T_{op}	Operating Temperature	-40 to 85	°C
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) V_{IN} from 30% to 70% of V_{CC} 2) $V_{CCA} = 2.7$ to $3.6V$; $V_{CCB} = 2.7$ to $5.5V$;DC SPECIFICATION FOR V_{CCA}

Symbol	Parameter	Test Condition			Value					Unit
		V _{CCA} (V)	V _{CCB} (V)		T _A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
V _{IHA}	High Level Input Voltage	2.7	3.0		2.0			2.0		V
		3.0	3.6		2.0			2.0		
		3.6	5.5		2.0			2.0		
V _{ILA}	Low Level Input Voltage	2.7	3.0				0.8		0.8	V
		3.0	3.6				0.8		0.8	
		3.6	5.5				0.8		0.8	
V _{OHA}	High Level Output Voltage	3.0	3.0	I _O =-100 μA	2.9	2.99		2.9		V
		3.0	3.0	I _O =-12 mA	2.56	2.85		2.46		
		3.0	3.0	I _O =-24 mA	2.35	2.65		2.25		
		2.7	3.0	I _O =-12 mA	2.3	2.5		2.2		
		2.7	4.5	I _O =-24 mA	2.1	2.3		2.0		
V _{OLA}	Low Level Output Voltage	3.0	3.0	I _O =100 μA		0.0	0.1		0.1	V
		3.0	3.0	I _O =24 mA		0.21	0.36		0.44	
		2.7	3.0	I _O =12 mA		0.11	0.36		0.44	
		2.7	4.5	I _O =24 mA		0.22	0.42		0.5	
I _{IA}	Input Leakage Current	3.6	5.5	V _I = V _{CC} or GND			± 0.1		± 1	μA
I _{OZA}	High Impedance Output Leakage Current	3.6	5.5	V _{IA} = V _{IHA} or V _{ILA} V _{IB} = V _{IHB} or V _{ILB} V _{I/OA} = V _{CCA} or GND			± 0.5		± 5	μA
I _{CCTA}	Quiescent Supply Current	3.6	5.5	V _{IA} = V _{CCA} or GND V _{IB} = V _{CCB} or GND			5		50	μA
I _{CCTAF}	Quiescent V _{CCA} Supply Current as B Port Floats	3.6	Open	V _{IA} = V _{CCA} or GND G= DIR = V _{CCA} V _{IB} = Open			5		50	μA
ΔI _{CCTA}	Maximum Quiescent Supply Current / Input (An, DIR, $\overline{G}$)	3.6	5.5	V _{IA} = V _{CCA} - 0.6V V _{IB} = V _{CCB} or GND			0.35		0.5	mA

DC SPECIFICATION FOR V_{CCB}

Symbol	Parameter	Test Condition			Value					Unit
		V _{CCA} (V)	V _{CCB} (V)		T _A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
V _{IHB}	High Level Input Voltage	2.7	3.0		2.0			2.0		V
		3.0	3.6		2.0			2.0		
		3.6	5.5		3.85			3.85		
V _{ILB}	Low Level Input Voltage	2.7	3.0				0.8		0.8	V
		3.0	3.6				0.8		0.8	
		3.6	5.5				1.65		1.65	
V _{OHB}	High Level Output Voltage	3.0	3.0	I _O =-100 μA	2.9	3.0		2.9		V
		3.0	3.0	I _O =-12 mA	2.56	2.85		2.46		
		3.0	3.0	I _O =-24 mA	2.35	2.65		2.25		
		3.0	4.5	I _O =-24 mA	3.86	4.25		3.76		
V _{OLB}	Low Level Output Voltage	3.0	3.0	I _O =100 μA		0.00	0.1		0.1	V
		3.0	3.0	I _O =24 mA		0.21	0.36		0.44	
		3.0	4.5	I _O =24 mA		0.18	0.36		0.44	
I _{IB}	Input Leakage Current	3.6	5.5	V _I = V _{CCA} or GND			± 0.1		± 1	μA
I _{OZB}	High Impedance Output Leakage Current	3.6	5.5	V _{IA} = V _{IHA} or V _{ILA} V _{I/OB} = V _{CCB} or GND			± 0.5		± 5	μA
I _{CCIB}	Quiescent Supply Current	3.6	5.5	V _{IA} = V _{CCA} or GND V _{IB} = V _{CCB} or GND			5		50	μA
ΔI _{CCIB}	Maximum Quiescent Supply Current / Input	3.6	5.5	V _{IA} = V _{CCA} or GND V _{IB} = V _{CCB} - 2.1V			1.35		1.5	mA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition			Value					Unit
		V _{CCA} (V)	V _{CCB} (V)		T _A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
V _{OLPA}	Dynamic Low Level Quiet Output (note 1, 2)	3.3	5.5			1.0	1.5			V
		3.3	5.5		-1.2	-0.6				
V _{OLPB}	Dynamic Low Level Quiet Output (note 1, 2)	3.3	5.5			0.8	1.2			V
		3.3	5.5		-0.8	-0.5				
V _{IHDA}	Dynamic High Voltage Input (note 1, 3)	3.3	5.5				2			V
V _{ILDA}	Dynamic Low Voltage Input (note 1, 3)	3.3	5.5		0.8					V
V _{IHDB}	Dynamic High Voltage Input (note 1, 3)	3.3	5.5				2			V
V _{ILDB}	Dynamic Low Voltage Input (note 1, 3)	3.3	5.5		0.8					V

1) Worst case package

2) Max number of output defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3V to threshold (V_{ILD}). 0V to threshold (V_{IHD}) $f = 1\text{ MHz}$

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Value										Unit
		V _{CCB} = 5 ± 0.5V					V _{CCB} = 3 ± 0.3V					
		T _A = 25 °C			-40 to 85 °C		-40 to 85 °C			-40 to 85 °C		
		Min.	Typ. (*)	Max.	Min.	Max.	Min.	Typ. (**)	Max.	Min.	Max.	
t _{PLH}	Propagation Delay Time An to Bn	1.0	4.8	8.0	1.0	8.5	1.0	5.5	8.5	1.0	9.0	ns
t _{PHL}		1.0	3.9	6.5	1.0	7.0	1.0	5.2	8.0	1.0	8.5	
t _{PZL}	Output Enable Time G̅ to Bn	1.0	4.7	8.0	1.0	8.5	1.0	6.0	9.0	1.0	9.5	ns
t _{PZH}		1.0	4.8	8.5	1.0	9.0	1.0	6.1	9.5	1.0	10.0	
t _{PLZ}	Output Disable Time G to Bn	1.0	4.0	8.0	1.0	8.5	1.0	6.3	9.5	1.0	10.0	ns
t _{PHZ}		1.0	3.8	7.5	1.0	8.0	1.0	4.5	8.0	1.0	8.5	
t _{PLH}	Propagation Delay Time Bn to An	1.0	3.8	6.5	1.0	7.0	1.0	4.4	7.0	1.0	7.5	ns
t _{PHL}		1.0	4.3	7.5	1.0	8.0	1.0	5.1	7.5	1.0	8.0	
t _{PZL}	Output Enable Time G̅ to An	1.0	5.9	9.5	1.0	10.0	1.0	6.4	10.0	1.0	10.5	ns
t _{PZH}		1.0	5.4	9.0	1.0	9.5	1.0	5.8	9.0	1.0	9.5	
t _{PLZ}	Output Disable Time G to An	1.0	4.6	9.5	1.0	10.0	1.0	5.2	9.5	1.0	10.0	ns
t _{PHZ}		1.0	3.1	6.5	1.0	7.0	1.0	3.4	6.5	1.0	7.0	
t _{OSLH} t _{OSHL}	Output To Output Skew Time (note1, 2)		1.0	1.5		1.5		1.5	1.5		1.5	ns

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$)

2) Parameter guaranteed by design

(*) Typical values at $V_{CCA} = 3.3V$, $V_{CCB} = 5.0V$

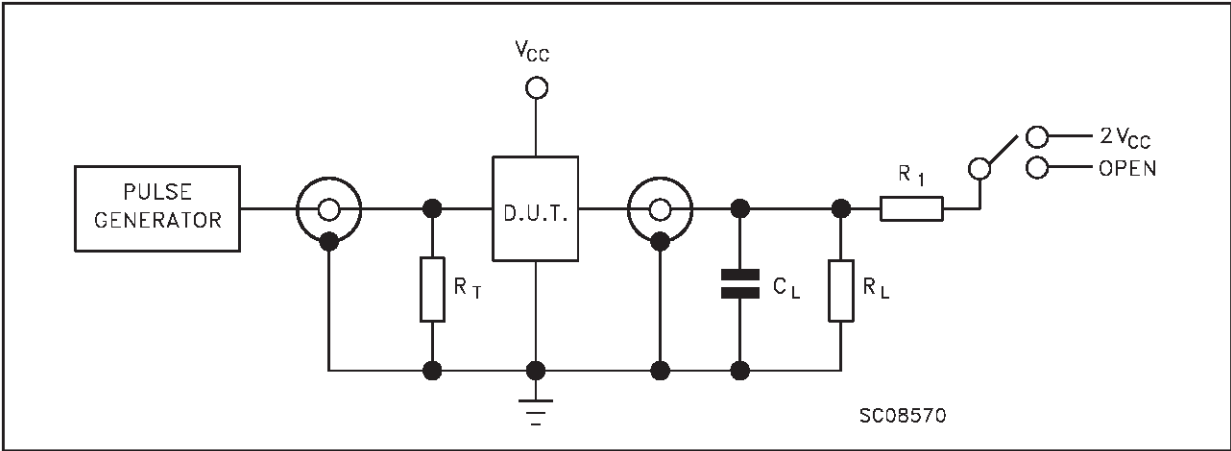
(**) Typical values at $V_{CCA} = 3.3V$, $V_{CCB} = 3.3V$

CAPACITANCE CHARACTERISTICS

Symbol	Parameter	Test Condition			Value					Unit
		V _{CCA} (V)	V _{CCB} (V)		T _A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
C _{INA}	Input Capacitance	open	open		4.5				V	
C _{I/O}	Input/Output Capacitance	3.3	5.0		10				V	
C _{PD}	Dynamic Low Level Quiet Output (note 1) A to B	3.3	5.0		55				V	
C _{PD}	Dynamic Low Level Quiet Output (note 1) B to A	3.3	5.0		40				V	

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per circuit)

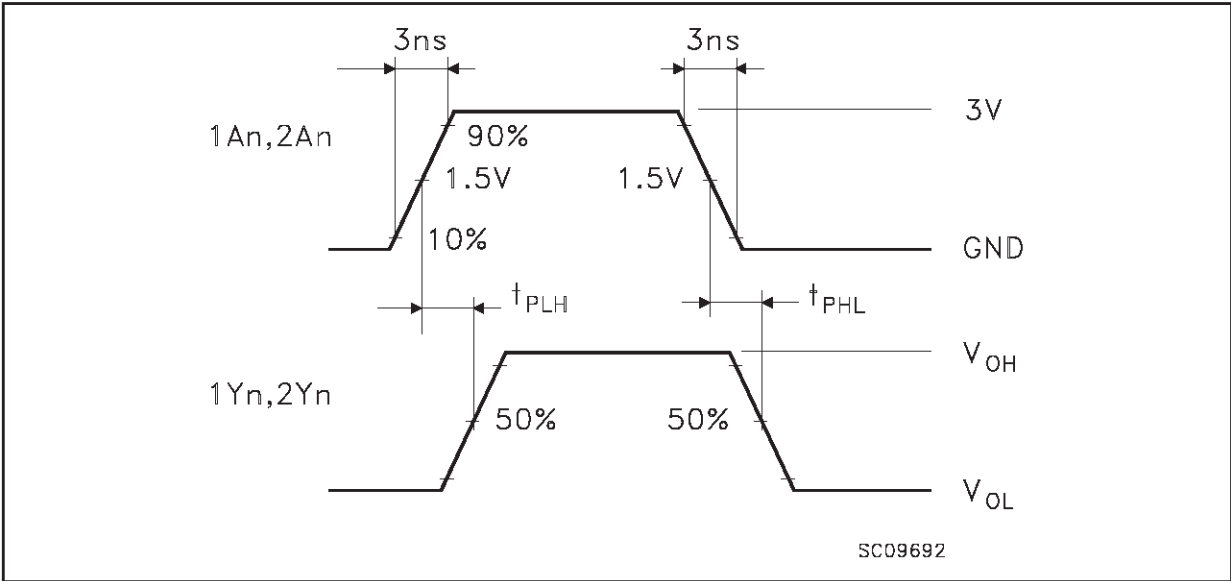
TEST CIRCUIT

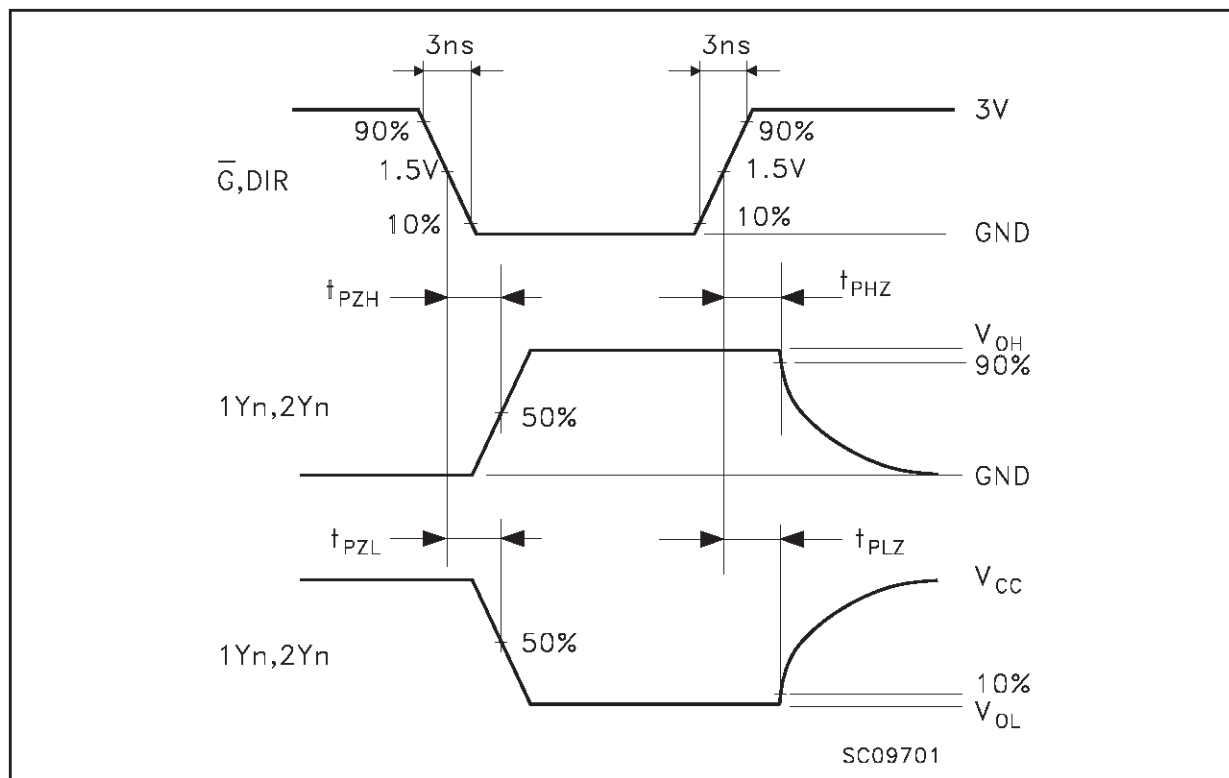


TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZLH}, t_{PLZ}	$2V_{CC}$
t_{PZH}, t_{PHZ}	Open

$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)
 $R_L = R_1 = 500\Omega$ or equivalent
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

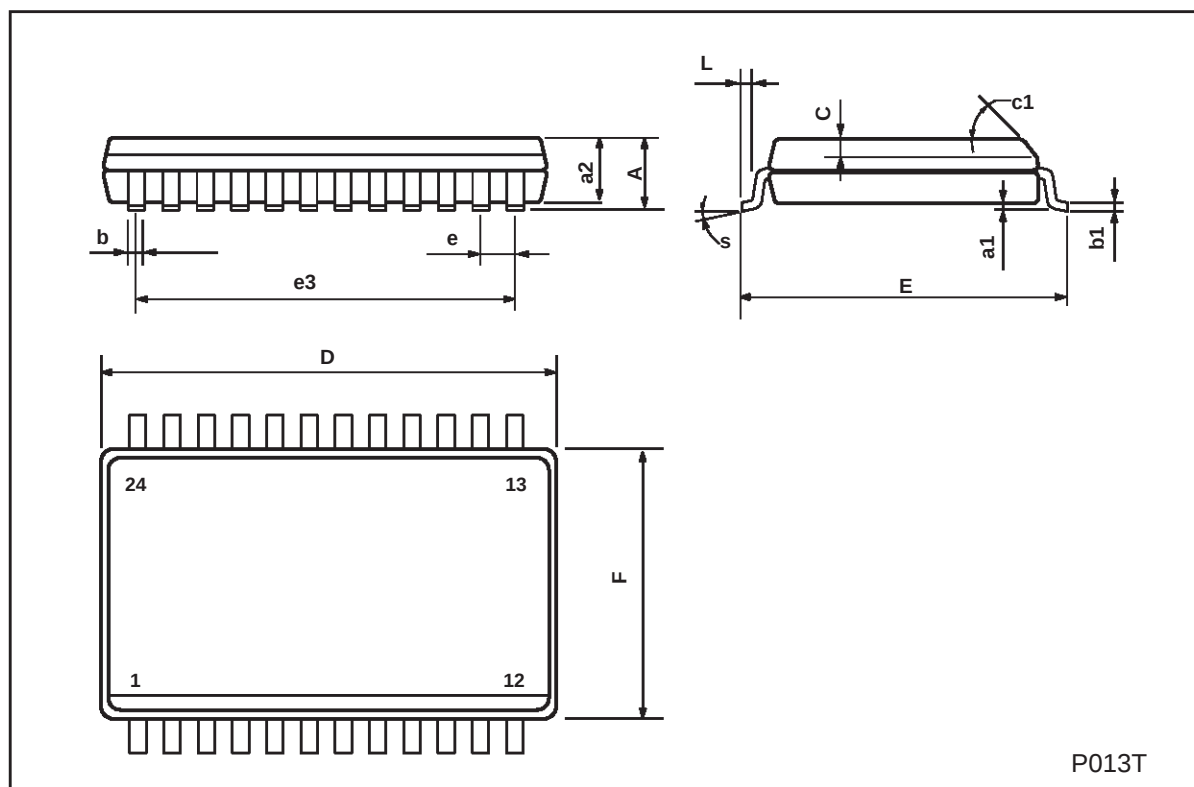
WAVEFORM 1: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)



WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME ($f=1\text{MHz}$; 50% duty cycle)

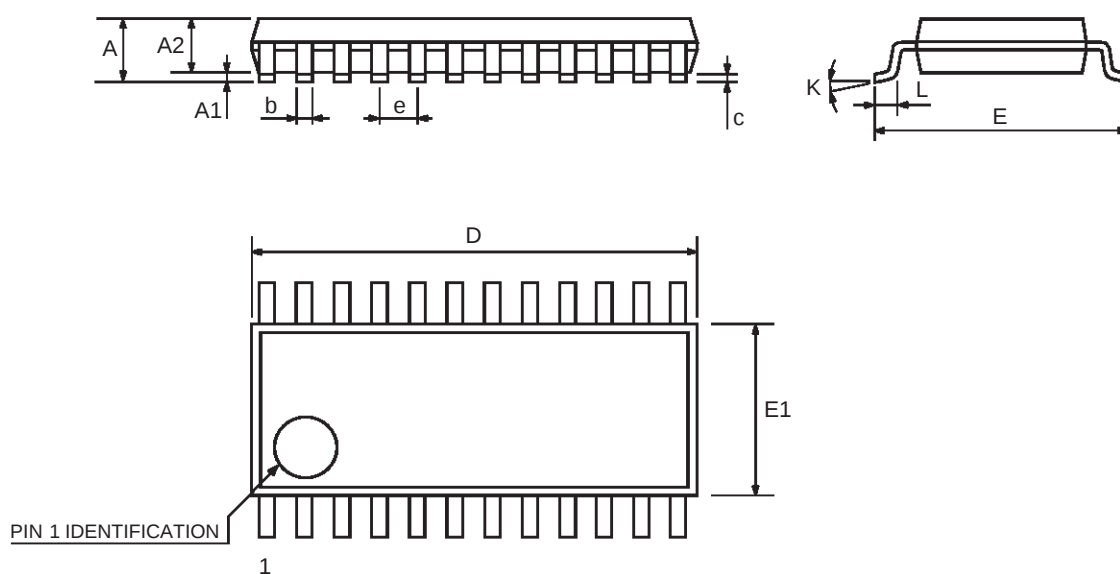
SO-24 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45 (typ.)					
D	15.20		15.60	0.598		0.614
E	10.00		10.65	0.393		0.420
e		1.27			0.05	
e3		13.97			0.55	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
S	8 (max.)					



TSSOP24 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.2	0.0035		0.0079
D	7.7	7.8	7.9	0.303	0.307	0.311
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°	4°	8°	0°	4°	8°
L	0.50	0.60	0.70	0.020	0.024	0.028



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